

# Citations for Ion : AJ

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1962</b>	Teplova, Ya. A. Nikolaev, V. S. Dimitriev, I. S. Fateeva, L. N. <b>'Slowing Down of Multicharged Ions in Solids and Gases'</b> <i>Zh. Eksp. Teor. Fiz., 42, 44-60 (1962)[Engl. Trans. Sov. Phys., Jetp 15, 31-41 (1962)]</i> <i>Comment : S, R.(75-1500 keV/amu) He, Li, Be, B, C, N, O, Ne, Na, Mg, Al, P, Cl, K, Br, Kr -&gt; H2, He, CH4, Benzene, Air, Ar, S. Same -&gt; Al, Ni, Ag, Au</i>	<b>1962-Tapl</b>
<b>1966</b>	Fastrup, B. Hvelplund, P. Sautter, C. A. <b>'Stopping Cross Section in Carbon of 0.1-1.0 MeV Atoms with 5&lt;Z&lt;20'</b> <i>Kgl. Danske Videnskab. Selskab. Mat. Fys. Medd., 35, No. 10, 1-28 (1966)</i> <i>Comment : S. (80-900 keV) H, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar-&gt;C</i>	<b>1966-Fast</b>
<b>1968</b>	Biersack, J. P. <b>'Range of Recoil Atoms in Isotropic Stopping Materials'</b> <i>Z. Physik, 211, 495-501 (1968)</i> <i>Comment : R. (96-1335 keV) Al, Na, Mn, Mg, Co, Cu, Ra -&gt; Al, Fe, Ni, Ar, Ne, O2, N2, CH4, He, H2, CuO, Al2O3</i>	<b>1968-Bier</b>
<b>1968</b>	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. <b>'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.'</b> <i>Phys. Rev., 165, 485-93 (1968)</i> <i>Comment : R, dR. Ion(Z1=12-81, E=0.22-5.2 MeV) -&gt; V, Ni, Zr, Au</i>	<b>1968-Bowm</b>
<b>1968</b>	Eisen, F. H. <b>'Channeling of Medium-Mass Ions through Silicon'</b> <i>Can. J. Phys., 46, 561-72 (1968)</i> <i>Comment : S. 100-500 keV B, C, N, O, F, Ne, Na, Mg, Al, Si, P, Cl, Ar, K -&gt; Si (Cryst.)</i>	<b>1968-Eise</b>
<b>1968</b>	Fastrup, B. Borup, A. Hvelplund, P. <b>'Stopping Cross Section in Atmospheric Air of 0.2 - 0.5 MeV Atoms with 6 &lt;= Z1 &lt;= 24.'</b> <i>Can. J. Phys., 46, 489-95 (1968)</i> <i>Comment : S. (100-1000 keV) C, N, O, Ne, N, Mg, P, S, Cl, Sc, Ca, Ti Al, Ar, K, Cr -&gt; Air</i>	<b>1968-Fast</b>
<b>1969</b>	Macdonald, J. R. Sidenius, G. <b>'The Total Ionization in Methane of Ions with 1 &lt;= Z1 &lt;= 20 at Energies from 10 to 120 keV'</b> <i>Phys. Letters A, 28, 543-44 (1969)</i> <i>Comment : S. 10-120 keV H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, Ca, V, Sc, Ti -&gt; CH4</i>	<b>1969-Macd</b>
<b>1971</b>	Crowder, B. L. <b>'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group III and Group V Ions Implanted into Silicon'</b> <i>J. Electrochem. Soc., 118, 943-52 (1971)</i> <i>Comment : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -&gt; Si</i>	<b>1971-Crow</b>

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<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1973</b>	Comas, J. Lucke, W. Addamiano, A. <b>'Ion Implanted Al Concentration Profiles in Unannealed and Annealed 6H-SiC'</b> <i>Bull. Am. Phys. Soc., 18, 606a (1973)</i> Comment : R, dR. 60 keV Al -> SiC	1973-Coma
<b>1973</b>	Dunning, K. L. Comas, J. Hubler, G. K. <b>'Depth Profiles of Aluminum Implanted into SiC. Nuclear Resonance Method.'</b> <i>Bull. Am. Phys. Soc., 18, 606b (1973)</i> Comment : R,dR. 60 keV Al -> SiC	1973-Dunn
<b>1973</b>	Dunning, K. L. Hubsher, G. K. Comas, J. Lucks, W. H. Hughes, H. L. <b>'Depth Profiles of Aluminum and Sodium Near Surfaces: Nuclear Resonance Method'</b> <i>Thin Solid Films, 19, 145-156 (1973)</i> Comment : R, dR. 60 keV Al -> SiC, 20, 60 keV Na -> SiO <sub>2</sub>	1973-Dunn2
<b>1974</b>	Blok, H. Kiely, F. M. Pate, B. D. Hanappe, F. Pelier, J. <b>'Further Measurement of the Track Length of Heavy Ions in Mica'</b> <i>Nucl. Inst. Methods, 119, 307-12 (1974)</i> Comment : R. (2.7-160 MeV) Al, Ar, Ca, Cr, Ni, Se, Kr, Ag -> Mica	1974-Blok
<b>1974</b>	Grant, W. A. Williams, J. S. Dodds, D. <b>'Measurement of Projected and Lateral Range Parameters for Low Energy Heavy Ions in Silicon by Rutherford Backscattering'</b> <i>Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 235-44 (1974)</i> Comment : R, dR, dR(Lateral). 10-80 keV Pb, 50-400 keV Bi, 40 keV Ar, Cu, Kr, Cd, Al, Dy, W -> Si	1974-Gran
<b>1975</b>	Lucke, W. Comas, J. Hubler, G. Dunning, K. <b>'Effect of Annealing on Profiles of Aluminum Implanted into Silicon Carbide'</b> <i>J. Appl. Phys., 46, 994-97 (1975)</i> Comment : R. 60 keV Al -> SiC	1975-Luck
<b>1976</b>	Armitage, B. H. Trehan, P. N. <b>'Energy Loss Straggling of Protons in Thick Absorbers'</b> <i>Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 55-63 (1976)</i> Comment : dS. 5-12 MeV H -> Al, V, Ni, Mo, Ag, Ta, Au	1976-Armi
<b>1976</b>	Braun, M. Emmoth, B. Buchta, R. <b>'Concentration Profiles and Sputtering Yields Measured by Optical Radiation of Sputtered Particles'</b> <i>Rad. Effects, 28, 77-83 (1976)</i> Comment : R, dR. 50-120 keV Al -> Ag; 60 keV Na -> Si	1976-Brau
<b>1976</b>	Dietrich, H. B. Comas, J. <b>'Anomalous Redistribution of Ion-Implanted Dopants'</b> <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 735-742 (1976)</i> Comment : R. 60 keV Al -> Si, 100 keV Be -> Si, GaAs	1976-Diet

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<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1976</b>	Dietrich, H. B. Weisenberger, W. H. Comas, J. <b>'Anomalous Migration of Ion-Implanted Al in Si'</b> <i>Appl. Phys. Letters, 28, 182-84 (1976)</i> Comment : <i>R,dR. 60 keV Al -&gt; Si</i>	<b>1976-Diet3</b>
<b>1976</b>	Forster, J. S. Ward, D. Andrews, H. R. Ball, G. C. Costa, G. J. <b>'Stopping Power Measurements for 19F, 24Mg, 27Al, 32S and 35Cl at Energies 0.2 to 3.5 MeV/Nucleon in Ti, Fe, Ni, Cu, Ag and Au.'</b> <i>Nucl. Inst. Methods, 136, 349-59 (1976).</i> Comment : <i>S. 2.2 MeV H, 0.2-3.5 MeV/amu F, Mg, Al, S, Cl -&gt; Ti, Fe, Ni, Cu, Ag, Au</i>	<b>1976-Fors</b>
<b>1976</b>	Myers, S. M. Smugeresky, J. E. <b>'Phase Equilibria and Diffusion in the Be-Al-Fe System using High Energy Ion Beams'</b> <i>Metal. Trans. A, 7, 795-802 (1976)</i> Comment : <i>R,dR. Al, Fe (30-50 keV) -&gt; Be</i>	<b>1976-Myer</b>
<b>1976</b>	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. <b>'Range Parameters of Heavy Ions in Silicon and Germanium with Released Energies from 0.01 &lt; epsilon &lt; 10'</b> <i>Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N.Y., P. 245-54 (1976)</i> Comment : <i>R, dR. (1-40 keV) Al, Sb, As, Ge, Au, Bi -&gt; Si, Ge</i>	<b>1976-Oetz</b>
<b>1977</b>	Anttila, A. Bister, M. Fontell, A. Winterbon, K. B. <b>'Ranges of Some Light Ions Measured by (p,gamma) Resonance Broadening'</b> <i>Rad. Effects, 33, 13-19 (1977)</i> Comment : <i>R. 20-100 keV 13C, 23Na, 26Mg, 27Al, 34S -&gt; Ta; 29Si -&gt; Al</i>	<b>1977-Antt</b>
<b>1978</b>	Alexander, T. K. Forster, J. S. Ball, G. C. Davies, W. G. Winterbon, K. B. <b>'Z1 and Z2 Variations in the Stopping Powers of Z1=10-18 Ions Deduced from DSAM Lifetime Measurements'</b> <i>Phys. Letters, 74B, 183-186 (1978)</i> Comment : <i>S. Ne, Na, Mg, Al, Si, P, S, Ar (3-4 MeV) -&gt; Cu, Ni, Ta, Au, Mg, Ca, Ti, Ba. Doppler shift lifetime measurements.</i>	<b>1978-Alex</b>
<b>1978</b>	Furuya, T. Nishi, H. Inada, T. Sakurai, T. <b>'Channeled-Ion Implantation of Group-III and Group-V Ions into Silicon'</b> <i>J. Appl. Phys., 49, 3918-3921 (1978).</i> Comment : <i>R, dR. 100-300 keV B, P, As, Al, Ga -&gt; Si [111], [110], Random</i>	<b>1978-Furu</b>
<b>1978</b>	Keinonen, J. Hautala, M. Luomajarvi, M. Anttila, A. Bister, M. <b>'Ranges of 27Al+ Ions in Nine Metals Measured by (p,gamma) Resonance Broadening'</b> <i>Rad. Effects, 39, 189-193 (1978)</i> Comment : <i>R, dR. 27Al -&gt; Ti, Ni, Cu, Mo, Ag, Ta, W, Au, Pb</i>	<b>1978-Kein</b>

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<b>1979</b>	Andrews, H. R. Lennard, W. N. Mitchell, I. V. Ward, D. Phillips, D. 'Low Energy Stopping Powers Determined by Time of Flight Techniques' <i>IEEE Trans. Nucl. Sci., NS-26, 1326-1330 (1979)</i> Comment : S. ( $0.180 < \text{vel.} < 0.219 \text{ cm/ns}$ ) ( $6 \leq ZI \leq 20$ ) -> C, Al, Ni, Ag, Au	<b>1979-Andr</b>
<b>1979</b>	Anttila, A. Hautala, M. 'Radiation Enhanced Outdiffusion During Ion Implantation' <i>Appl. Phys., 19, 199-203 (1979)</i> Comment : R, dR. 40 keV 27Al -> Au	<b>1979-Antt</b>
<b>1979</b>	Bister, M. Hautala, M. Jantti, M. 'Comparison of Experimental and Theoretical Ranges of Heavy Ions in the Low Energy Region' <i>Rad. Effects, 42, 201-208, (1979)</i> Comment : R, dR. 20-190 keV Eu, Cs, La, Au, Al -> Si, Al, Ti, Ta	<b>1979-Bist</b>
<b>1979</b>	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)</i> Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si	<b>1979-Sant</b>
<b>1979</b>	Ward, D. Andrews, H. R. Mitchell, I. V. Lennard, W. N. Walker, R. B. 'Systematics for the Z1-Oscillation in Stopping Powers of Various Solid Materials' <i>Can. J. Phys., 57, 645-656 (1979).</i> Comment : S. ( $\text{vel.}=0.18-0.22 \text{ cm/ns}$ ) C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Ca -> C, Al, Ni, Ag, Au	<b>1979-Ward</b>
<b>1980</b>	Campbell, A. B. Sartwell, B. D. Needham, P. B. Jr. 'Depth Profiling of Ion-Implanted Alloys' <i>J.Appl. Phys., 50, 283-289 (1980)</i> Comment : R, dR. 25 keV Ni, Cr, Al -> Fe	<b>1980-Camp</b>
<b>1980</b>	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. 'Charge-Exchange Effects in Energy-Loss Straggling' <i>Nucl. Inst. Methods, 170, 221-225 (1980)</i> Comment : R, dR. 0-50 MeV Atomic Numbers I-16 -> Al	<b>1980-Sofi</b>
<b>1981</b>	Muminov, A. I. Akilov, F. S. 'Determination of Stopping Cross Sections for 7Li, 12C, 23Na, 26Mg and 27Al by the Doppler Broadening of Gamma-Rays Emitted by these Nuclei' <i>Sov. J. Nucl. Phys., 34 (1), 7-10 (1981)</i> Comment : S. Li, C, Na, Mg, Al (25 keV/amu) -> 75 elements and compounds	<b>1981-Mumi</b>
<b>1983</b>	Mannsperger, H. Kalbitzer, S. Demond, F. J. Damjantschitsch, H. 'Projection Factors of Low Energy Ion Ranges' <i>Nucl. Inst. Methods, 209/210, 49-55 (1983)</i> Comment : R. H, C, Na, Al, Si, Ar, Cr ( $.04 < \epsilon < 1$ ) -> Si, Ge	<b>1983-Mann</b>

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<b>1983</b>	Wach, W. Wittmaack, K. <b>'Ranges of Low Energy Light Ions in Amorphous Silicon'</b> <i>Phys. Rev. B, 27 (6), 3528-3537 (1983)</i> <i>Comment : R, dR. Li, B, N, O, F, Na, Mg, Al ((1-20 keV) -&gt; Si</i>	<b>1983-Wach</b>
<b>1986</b>	Lennard, W. N. Geissel, H. Phillips, D. Jackson, D. P. <b>'Heavy Ion Straggling: Possible Evidence for Inner-Shell Excitation'</b> <i>Phys. Rev. Letters, 57, 318-320 (1986)</i> <i>Comment : dS.F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Sc (16 keV/amu) -&gt; C</i>	<b>1986-Lenn</b>
<b>1986</b>	Lennard, W. N. Geissel, H. Jackson, D. P. Phillips, D. <b>'Electronic Stopping Values for Low Velocity Ions (9 &lt;= Z1 &lt;= 92) in Carbon Targets'</b> <i>Nucl. Inst. Methods, B13, 127 (1986)</i> <i>Comment : S. (16 keV/amu) F, Ne, Na, Mg, Al, P, Cl, Ar, K, Sc, Cr, Mn, Cu, Kr, Nb, Ag, In, Xe, Sm, Yb, Au, Bi, U -&gt; C</i>	<b>1986-Lenn2</b>
<b>1986</b>	Wilson, R. G. <b>'Random and Channeled Implantation Profiles and Range Parameters for P and Al in Crystalline and Amorphized Si'</b> <i>J. Appl. Phys., 60 (8), 2797-2805 (1986)</i> <i>Comment : R, dR. P, Al (25-600 keV) -&gt; Si</i>	<b>1986-Wils</b>
<b>1987</b>	Keinonen, J. Kuronen, A. Hautala, M. Karttunen, V. Lappalainen, R. <b>'Velocity Dependence in Low-Velocity Electronic Stopping Power of Heavy Ions'</b> <i>Phys. Letters A, 123 (6), 307-310 (1987)</i> <i>Comment : S, R, Al, Si (100-820 keV) -&gt; Ta (Ranges at 5, 12 MeV)</i>	<b>1987-Kein</b>
<b>1988</b>	Wilson, R. G. <b>'(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe'</b> <i>J. Appl. Phys., 63, 5302-5311 (1988)</i> <i>Comment : R, dR. 45 Ions (H to Ta) at 100-700 keV -&gt; HgCdTe</i>	<b>1988-Wils</b>
<b>1988</b>	Wilson, R. G. <b>'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe'</b> <i>J. Crystal Growth, 86, 735-743 (1988)</i> <i>Comment : R, dR. 52 Ions (H-Hg) at 100-700 keV -&gt; CdTe, HgCdTe</i>	<b>1988-Wils2</b>
<b>1989</b>	Tikkanen, P. <b>'Electronic Stopping Power of Ta for Z=11-18 Atoms at Energies 0-0.8 MeV/amu'</b> <i>Nucl. Inst. Methods, B36, 103 (1989)</i> <i>Comment : S, Na, Mg, Al, Si, P, S, Cl, Ar (0-0.8 MeV/amu) -&gt; Ta</i>	<b>1989-Tikk</b>
<b>1990</b>	Raisanen, J. Rauhala, E. <b>'Stopping Powers and Energy Loss of Mylar, Kapton, Havar and Ni for 10 Ions (Z=3-17) in the Energy Range 0.2-2.1 MeV/amu'</b> <i>Phys. Rev. B, 41, 3951-3958 (1990)</i> <i>Comment : S, B, C, N, O, Al, Si, P, Cl (0.2-2.1 MeV/amu) -&gt; Mylar, Kapton, Havar, Ni</i>	<b>1990-Rais</b>

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<b>1991</b>	Abdesselam, A. Stoquert, J. P. Guillaume, G. Hage-Ali, M. Grob, J. J. <b>'Slowing Down of Heavy Ions in Solids near the Stopping Power Maximum'</b> <i>Nucl. Inst. Methods, B56/57, 355-357 (1991)</i> Comment : S. C, O, Al, Cu, Ti, I, Ag, Au (0.2-2 MeV/amu) -> C, Al, Cu, Ag, Ta, Au	1991-Abde
<b>1991</b>	Abdesselam, N. Stoquert, J. P. Guillaume, G. Hage-Ali, M. Grob, J. J. <b>'Stopping Power of C and Al Ions in Solids'</b> <i>Nucl. Inst. Methods, B61, 385-393 (1991)</i> Comment : S. C, Al (.2-2 MeV/amu) -> C, Al, Cu, Ag, Ta and Au	1991-Abde2
<b>1991</b>	Kuronen, A.	1991-Kuro
<b>1991</b>	'A Study of Stopping Power using Nuclear Methods' <i>Comm. Physico-Math. (Finland), 122, 1-36 (1991)</i> Comment : S. Ion [Z=3-22] at (0-0.4 Vo) -> Solids (Z=14-82)	
<b>1991</b>	McGuire, E. J. <b>'The Proton Stopping Power of Aluminum and Nickel ions'</b> <i>J. Appl. Phys., 70, 7213-7216 (1991)</i> Comment : Theory	1991-McGu
<b>1992</b>	Lennard, W. A. Xia, Yueyuan Geissel, H. <b>'Impact Parameter Dependent Electronic Stopping for Low Velocity Heavy Ions'</b> <i>Nucl. Inst. Methods, B67, 44-49 (1992)</i> Comment : S. Al (0.8Vo) -> C Stopping vs. angular scatter.	1992-Lenn
<b>1994</b>	Fageeha, O. Howard, J. Block, R. C. <b>'Distribution of Radial Energy Deposition around the Track of Energetic Charged Particles in Silicon'</b> <i>J. Appl. Phys., 75, 2317-2321 (1994)</i> Comment : S. C, Al, Fe (10-10,000 MeV) -> Si	1994-Fage
<b>1994</b>	Raisanen, J. Rauhala, E. Fulop, Z. Kiss, A. Z. Somorjai, E. <b>'Stopping Powers of CR-39 Nuclear Track Material for Z=1-14 Ions with 0.25-2.8 MeV/amu'</b> <i>Rad. Meas. (UK), 23, 749-752 (1994)</i> Comment : S. Z=1-14 (0.25-2.8 MeV/amu) -> CR-39	1994-Rais2
<b>1995</b>	Randhawa, G. S. Garg, A. K. Virk, H. S. <b>'Range Study of Heavy Ions in Plastic Track Detectors'</b> <i>Rad. Meas. (UK), 24, 197-199 (1995)</i> Comment : R. Heavy Ions (10-17 MeV/amu) -> Lexan	1995-Rand
<b>1995</b>	Sharma, S. K. Kumar, S. Sharma, A. P. <b>'Range of Heavy Ions in Solids'</b> <i>Appl. Rad. Isotopes (UK), 46, 1345-1350 (1995)</i> Comment : R. Fe, Al, Ni (99.5, 123, 199 MeV/amu) -> CR-39, Lexan	1995-Shar

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<b>1996</b>	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. <b>'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions'</b> <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> Comment : <i>S. Channeling of ions He to Kr in Si &lt;110&gt;</i>	<b>1996-Gelf</b>
<b>1996</b>	Hari, K. V. Pathak, A. P. Sharma, S. K. Shyam, K. Nath, N. <b>'Energy Loss of MeV Heavy Ions in Carbon'</b> <i>Nucl. Inst. Methods, B108, 223-226 (1996)</i> Comment : <i>S. Z1 (O - Cu) at 0.1-1.0 MeV/amu -&gt; C</i>	<b>1996-Hari</b>
<b>1997</b>	Jokinen, J. <b>'Stopping Powers of C, Al and Cu for use in ERDA Analyses with Probing MeV-Energy Au Ions'</b> <i>Nucl. Inst. Methods, B124, 447-452 (1997)</i> Comment : <i>S. Au, C, Al, Au -&gt; C, Al, Cu</i>	<b>1997-Joki2</b>
<b>2000</b>	Sharma, A. Kumar, S. Sharma, S. K. Diwan, P. K. Nath, N. <b>'Stopping Power of Mylar for Heavy Ions up to Copper'</b> <i>Nucl. Inst. Methods, B170, 323-328 (2000)</i> Comment : <i>S. Na,Al,Cl,Sc,Ti,V,Cr,Mn,Ni,Cu (0.3 - 2.3 MeV/u) -&gt; Mylar</i>	<b>2000-Shar</b>
<b>2001</b>	Zhang, Y. Possnert, G. Whitlow, H. J. <b>'Measurements of the Mean Energy-Loss of Swift Heavy Ions in Carbon with High Precision'</b> <i>Nucl. Inst. Methods, B183, 34-37 (2001)</i> Comment : <i>S. Li,Be, B, C, N, O, F,Na,Mg,Al,Si,Cr,Mn,Fe (100 - 800 keV/u) -&gt; C</i>	<b>2001-Zhan</b>
<b>2002</b>	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T. D. Zhang, Y. <b>'Measurement and Uncertainties of Energy Loss in Silicon over a Wide Z1 Range using Time-of-Flight Detector Telescopes'</b> <i>Nucl. Inst. Methods, B195, 133-146 (2002)</i> Comment : <i>S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, P, Mn, Fe -&gt; Si</i>	<b>2002-Whit2</b>
<b>2002</b>	Zhang, Y. <b>'High-Precision Measurement of Electronic Stopping Powers for Heavy Ions using High-Resolution Time-of-Flight Spectrometry'</b> <i>Nucl. Inst. Methods, B196, 1-15 (2002)</i> Comment : <i>S. Stopping of 18 Heavy Ions into C, Al and Au Targets</i>	<b>2002-Zhan</b>
<b>2002</b>	Zhang, Y. Possnert, G. <b>'Electronic Stopping Power of Swift Heavy Ions in Carbon'</b> <i>Nucl. Inst. Methods, B190, 69-73(2002)</i> Comment : <i>S. He, Be, C and Al -&gt; C</i>	<b>2002-Zhan2</b>
<b>2003</b>	Zhang, Yanwen Weber, W. J. <b>'Electronic stopping of He, B, N, and Al in SiC'</b> <i>Appl. Phys. Lett. 83, 1665 (2003)</i> Comment : <i>S. He, B, N, Al (0.5 -0.6 MeV/n) -&gt; SiC</i>	<b>2003-Zha2</b>

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2004	Zhang, Y. Weber, W. J. <b>'Studies of Electronic Stopping Powers using Time of Flight Spectrometry'</b> <i>Nucl. Inst. Methods, B219-220, 256-262 (2004)</i> Comment : S. He, O, Al -> C, SiC	2004-Zha1
2004	Zhang, Y. Weber, W. Whitlow, H. J. <b>'Electronic Stopping Powers for Heavy Ions in Silicon'</b> <i>Nucl. Inst. Methods, B215, 48-56 (2004)</i> Comment : S. 14 light ions (Be-Cu) -> Si	2004-Zha3
2005	Pascual-Izarra, C. Garcia, G. <b>'Experimental stopping forces for He, C, O, Al and Si ions in Al<sub>2</sub>O<sub>3</sub> in the energy range of 40–1250 keV/nucleon '</b> <i>Nucl. Instr. Methods B228, 388 (2005)</i> Comment : S. He,C,O,Al (40 - 1250 keV/n) -> Al <sub>2</sub> O <sub>3</sub>	2005-Pasc
2005	Zhang, Yanwen Weber, W. J. McCready, D.E. Grove, D.A. Jensen, J. <b>'Experimental determination of electronic stopping for ions in silicon dioxide'</b> <i>Appl. Phys. Lett. 87, 104103 (2005)</i> Comment : S. Be - Si (0.05 - 1.3 MeV/n) -> SiO <sub>2</sub>	2005-Zha2
2010	Msimanga, M. Comrie, C.M. Pineda-Vargas, C.A. Murray, S. <b>'Experimental stopping powers of Al, Mg, F and O ions in ZrO<sub>2</sub> in the 0.1-0.6MeV/u energy range'</b> <i>Nucl. Instrum. Methods B 268, 1772 (2010)</i> Comment : S. Al (0.13-0.48 MeV/u), F (0.14-0.55 MeV/u), Mg (0.14-0.50 MeV/u), O (0.16-0.63 MeV/u) -> ZrO <sub>2</sub>	2010-Msim